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## High power PNP epitaxial planar bipolar transistor

### Features

- High breakdown voltage  $V_{CE0} = -100\text{ V}$
- Complementary to 2STC2510
- Typical  $f_t = 20\text{ MHz}$
- Fully characterized at  $125\text{ }^\circ\text{C}$

### Application

- Audio power amplifier

### Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

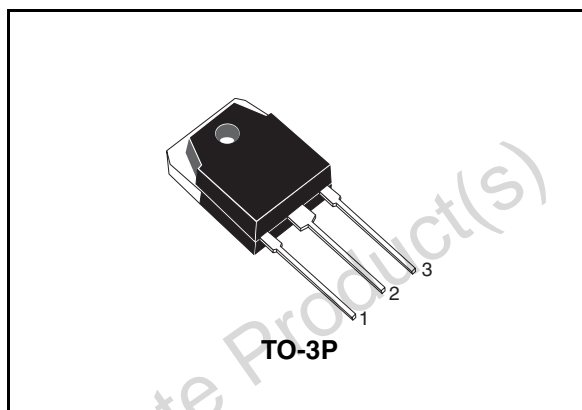


Figure 1. Internal schematic diagram

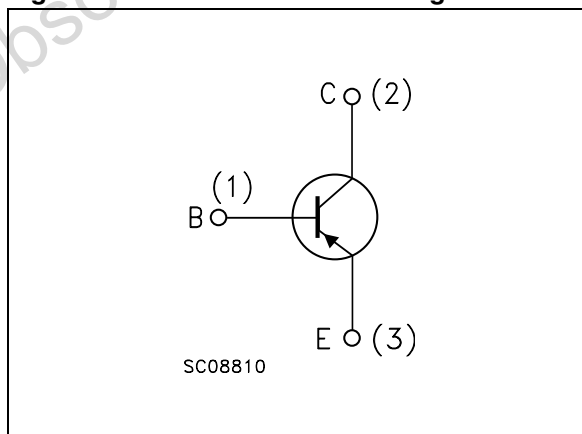


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA2510	2STA2510	TO-3P	Tube

# 1 Electrical ratings

**Table 2. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	-100	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	-100	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	-6	V
$I_C$	Collector current	-25	A
$I_{CM}$	Collector peak current ( $t_P < 5$ ms)	-50	A
$P_{TOT}$	Total dissipation at $T_C = 25$ °C	125	W
$T_{stg}$	Storage temperature	-65 to 150	°C
$T_J$	Max. operating junction temperature	150	°C

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	°C/W

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ °C}$ ; unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = -100\text{ V}$			-10	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = -6\text{ V}$			-10	$\mu\text{A}$
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = -50\text{ mA}$	-100			V
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage ( $I_{\text{E}} = 0$ )	$I_{\text{C}} = -100\text{ }\mu\text{A}$	-100			V
$V_{(\text{BR})\text{EBO}}^{(1)}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = -1\text{ mA}$	-6			V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = -12\text{ A}$ $I_{\text{B}} = -1.2\text{ A}$			-1.5	V
$V_{\text{BE}}^{(1)}$	Base-emitter voltage	$V_{\text{CE}} = -4\text{ V}$ $I_{\text{C}} = -12\text{ A}$			-1.8	V
$h_{\text{FE}}$	DC current gain	$I_{\text{C}} = -12\text{ A}$ $V_{\text{CE}} = -4\text{ V}$	40		80	
$f_{\text{T}}$	Transition frequency	$I_{\text{C}} = -0.5\text{ A}$ $V_{\text{CE}} = -12\text{ V}$		20		MHz

1. Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 1.5\%$

## 2.1 Electrical characteristic (curves)

Figure 2. Safe operating area

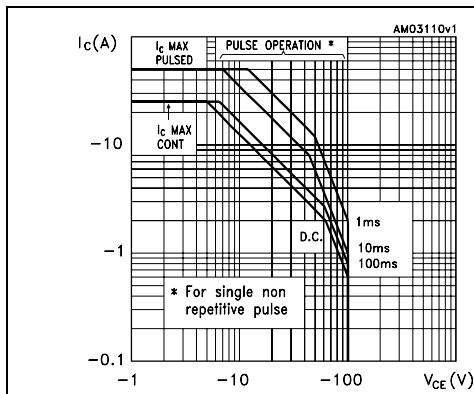


Figure 3. Derating curve

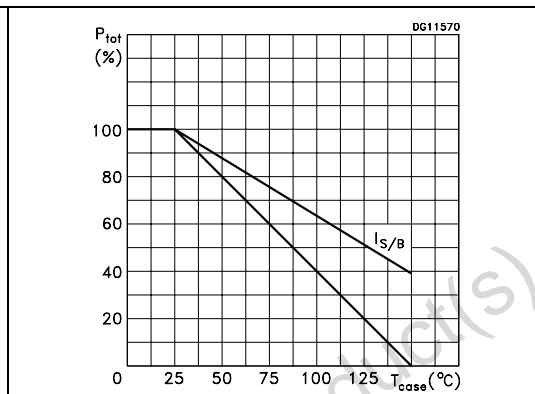


Figure 4. Output characteristics

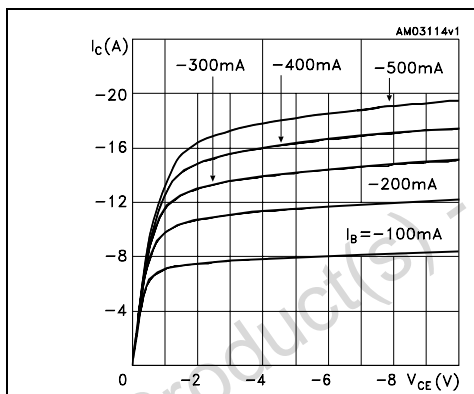


Figure 5. DC current gain

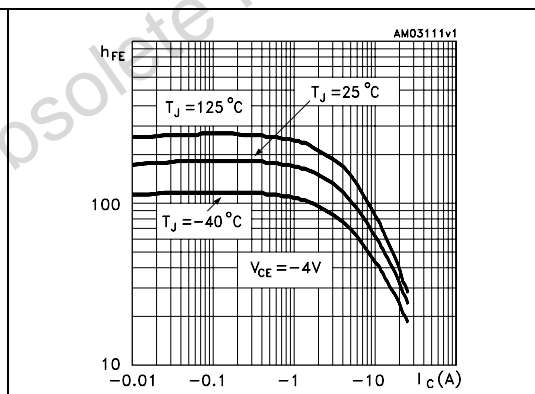


Figure 6. Collector-emitter saturation voltage

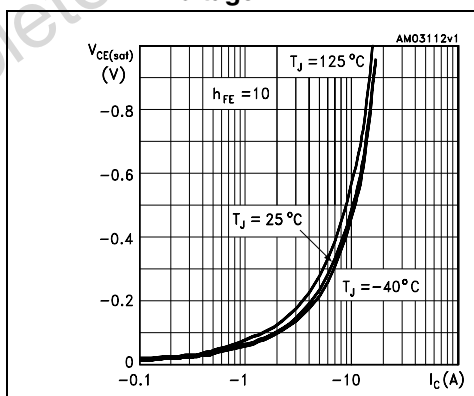
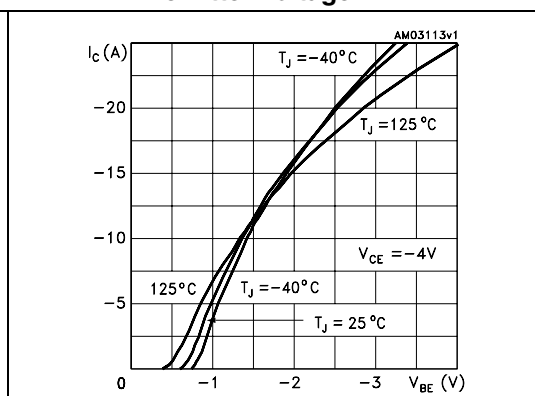


Figure 7. Collector current vs base-emitter voltage



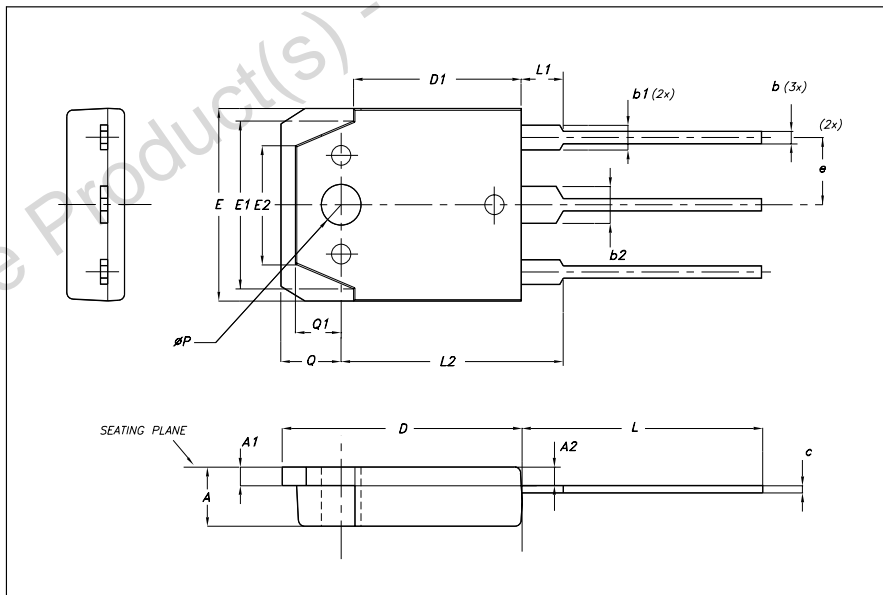
### 3 Package mechanical data

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**TO-3P Mechanical data**

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
P	3.10		3.30
Q		5	
Q1		3.80	



## 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
26-Nov-2007	1	Initial release
16-May-2008	2	Document status promoted from preliminary data to datasheet.
14-Nov-2008	3	Added paragraph: <a href="#">Electrical characteristic (curves) on page 4.</a>

Obsolete Product(s) - Obsolete Product(s)



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